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Electronic Version v1.1

Stylesheet Version v1.1.0

Title of
Invention

Method for Manufacturing Buried Insulating Layer Type Single Crystal Silicon Carbide Substrate and Manufacturing Device for the Same

Application Number:

Date:

First Named Applicant:

Katsutoshi IZUMI

Confirmation Number:

Attorney Docket Number:

040091

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Documents being submitted:	Files
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us-assignment	U040091-usassn.xml
40 400ig	us-assignment.xsl
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